

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	30	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	l _D	6.0 4.8	А
	t < 10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	l _D	7.5 5.9	А
Continuous Drain Current (Note E) V 4 EV	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	l _D	5.0 4.0	А
Continuous Drain Current (Note 5) V _{GS} = 4.5V	t < 10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	6 4.8	А
Maximum Body Diode Forward Current (Note 5)	Is	2	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	31	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	C-	1.75	W
Total Fower Dissipation (Note 5)	$T_A = +70^{\circ}C$	P_D	1.1	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	0	72	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t < 10s	$R_{\theta JA}$	50	
Thermal Resistance, Junction to Case (Note 5)	$R_{ heta JC}$	23		
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

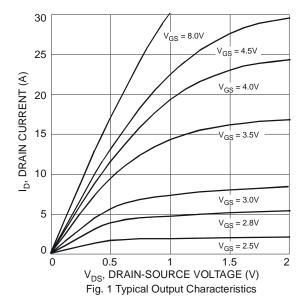
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

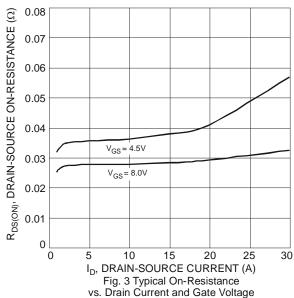
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(TH)}	1	1.5	2	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance			22	30	mΩ	$V_{GS} = 10V, I_D = 7A$	
Static Diani-Source On-Nesistance	R _{DS(ON)}		32	42	11122	$V_{GS} = 4.5V, I_D = 5.6A$	
Forward Transfer Admittance	Y _{fs}		10	_	S	$V_{DS} = 5V, I_{D} = 7A$	
Diode Forward Voltage	V_{SD}	_	0.75	1.0	V	$V_{GS} = 0V$, $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss		498	_		V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz	
Output Capacitance	Coss	_	52	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	45	_			
Gate Resistance	R _G	_	2.4	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge	Q_g	_	11.4	_		V _{GS} = 10V, V _{DS} = 15V, I _D = 5.8A	
Gate-Source Charge	Qgs	_	1.4	_	nC		
Gate-Drain Charge	Q _{gd}	_	2	_			
Turn-On Delay Time	t _{D(ON)}	_	3.4	_		$V_{DD} = 15V, V_{GS} = 10V,$ $R_L = 2.6\Omega, R_G = 3\Omega$	
Turn-On Rise Time	t _R	_	6.2	_			
Turn-Off Delay Time	t _{D(OFF)}	_	13.9		ns		
Turn-Off Fall Time	t _F	_	2.8	_			

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
- 6. Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to production testing.







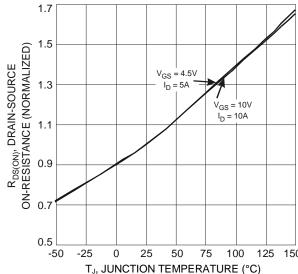
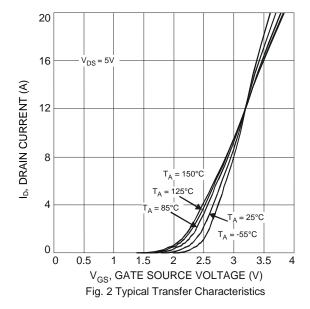


Fig. 5 On-Resistance Variation with Temperature



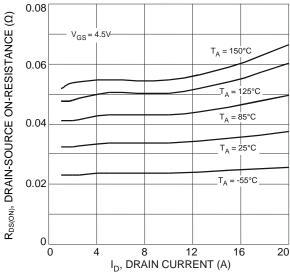


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

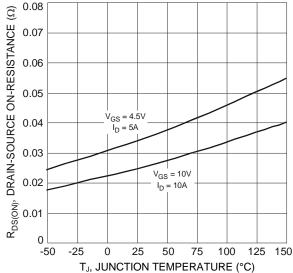


Fig. 6 On-Resistance Variation with Temperature



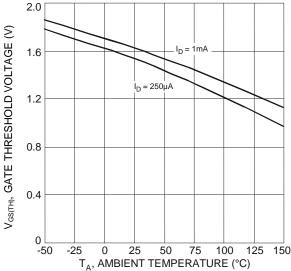
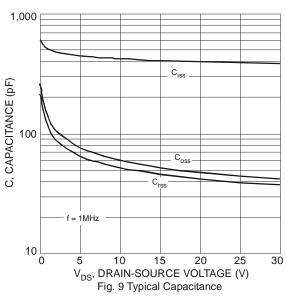
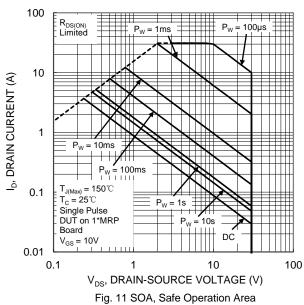
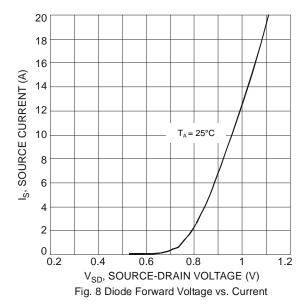
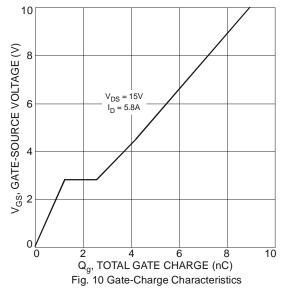


Fig. 7 Gate Threshold Variation vs. Ambient Temperature











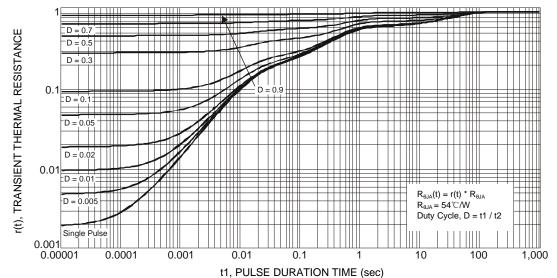


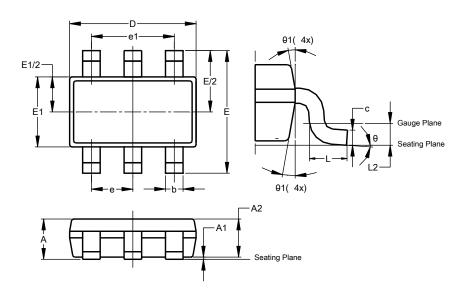
Fig. 12 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26

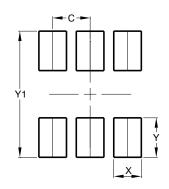


TSOT26					
Dim	Min	Max	Тур		
Α	-	1.00	-		
A1	0.010	0.100	-		
A2	0.840	0.900	-		
D	2.800	3.000	2.900		
Е	2.800 BSC				
E1	1.500	1.700	1.600		
b	0.300	0.450	-		
С	0.120	0.200	-		
е	0.950 BSC				
e1	1.900 BSC				
L	0.30	0.50	_		
L2	0.250 BSC				
θ	0°	8°	4°		
θ1	4°	12°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26



Dimensions	Value (in mm)			
С	0.950			
X	0.700			
Y	1.000			
Y1	3 199			



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